

ABSTRACT OF THE DISCLOSURE

First and second impurity doped regions are formed in a semiconductor substrate. A first gate electrode is formed on the first impurity doped region with a first gate insulation film interposed therebetween. 5 A second gate electrode is formed on the second impurity doped region with a second gate insulation film interposed therebetween. A first sidewall insulation film is formed on either side of the first gate electrode. A second sidewall insulation film has a thickness different from that of the first sidewall insulation film and are formed on either side of the second gate electrode. A third sidewall insulation film is formed on the first sidewall insulation film on 10 the side of the first gate electrode. A fourth sidewall insulation films have a thickness different from that of the third sidewall, insulation film and are formed on the second sidewall insulation film on the side of the second gate electrode. 15